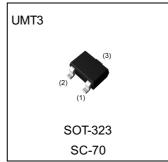


Medium power transistor (60V, 0.5A)

Parameter	Value	
$V_{CEO}$	60V	
IC	500mA	

## Outline



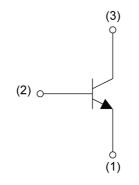
#### Features

1)High speed switching. (Tf:Typ.:80ns at I<sub>C</sub>=500mA)

2)Low saturation voltage, typically (Typ.:150mV at I<sub>C</sub>=100mA, I<sub>B</sub>=10mA)

- 3)Strong discharge power for inductive load and capacitance load.
- 4)Complements the 2SA2088.

### •Inner circuit



- (1) Emitter
- (2) Base
- (3) Collector

# Application

LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

# Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SC5876	UMT3	2021	T106	180	8	3000	VS

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Values	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	60	V
Emitter-base voltage	$V_{EBO}$	6	V
Calle stem as unwent	I <sub>C</sub>	500	mA
Collector current	I <sub>CP</sub> *1	1.0	Α
Power dissipation	P <sub>D</sub> *2	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C

# • Electrical characteristics $(T_a = 25^{\circ}C)$

Parameter	Cumbal	Conditions	Values			Unit
Parameter	Parameter Symbol Conditions		Min.	Тур.	Max.	Offic
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 100μA	60	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	60	ı	ı	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = 100μA	6	1	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V	-	-	1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	1	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA	-	150	300	mV
DC current gain	h <sub>FE</sub>	$V_{CE}$ = 2V, $I_{C}$ = 50mA	120	-	390	-
Transition frequency	f <sub>T</sub> *3	$V_{CE} = 10V, I_{E} = -100mA,$ f = 100MHz	-	300	-	MHz
Output capacitance	C <sub>ob</sub>	$V_{CB} = 10V$ , $I_E = 0$ mA, f = 1MHz	-	5	-	pF
Turn-On time	t <sub>on</sub> *3	I <sub>C</sub> = 500mA, I <sub>B1</sub> = 50mA,	-	70	-	ns
Storage time	t <sub>stg</sub> *3	$I_{B2} = -50 \text{mA},$ $V_{CC} \approx 25 \text{V},$	-	130	-	ns
Fall time	t <sub>f</sub> *3	$R_L = 50\Omega$ See test circuit	-	80	-	ns

## hFE values are calssified as follows:

rank	Q	R	-	-	-
hFE	120-270	180-390	-	-	-

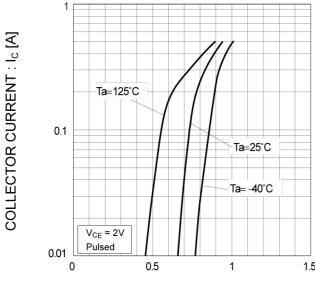
<sup>\*1</sup> Pw=10ms

<sup>\*2</sup> Each terminal mounted on a reference land.

<sup>\*3</sup> Pulsed

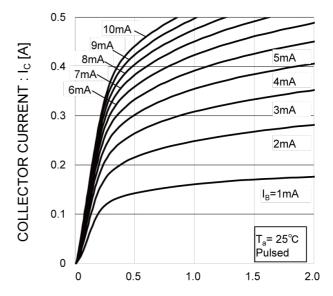
# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.1 Ground Emitter Propagation Characteristics



BASE TO EMITTER VOLTAGE : VBE [V]

Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: V<sub>CE</sub> [V]

Fig.3 DC Current Gain vs. Collector Current (I)

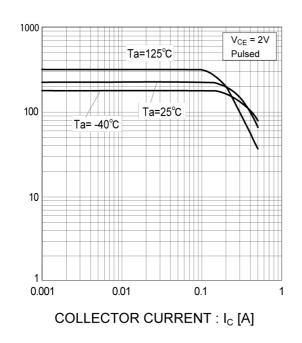
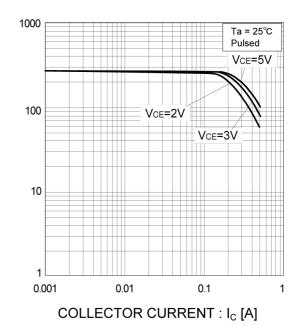


Fig.4 DC Current Gain vs. Collector Current (II)



DC CURRENT GAIN: hee

DC CURRENT GAIN: hFE

# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

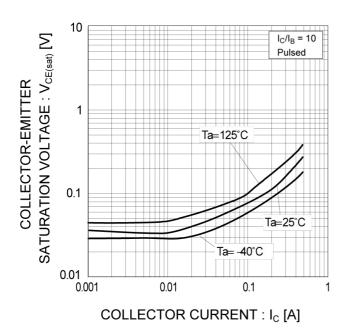
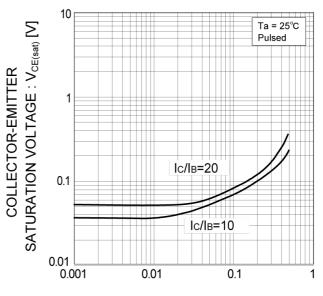


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)



COLLECTOR CURRENT : I<sub>C</sub> [A]

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

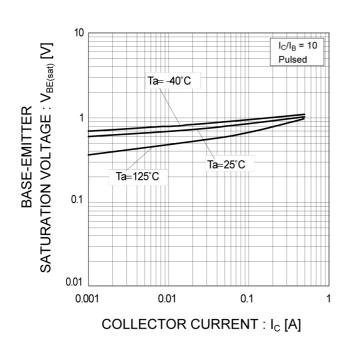
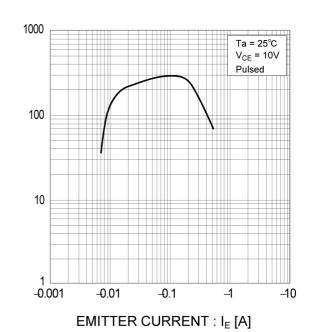


Fig.8 Transition Frequency



TRANSITION FREQUENCY  $: \mathsf{f}_\mathsf{T} \left[ \mathsf{MH}_\mathsf{Z} 
ight]$ 

# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig. 0. Calla atau autuut Canaaitanaa

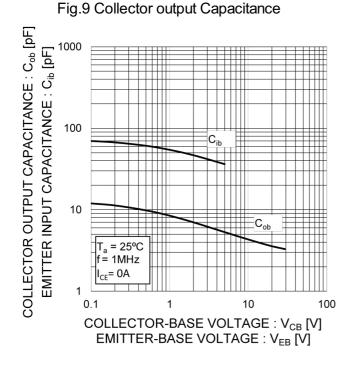
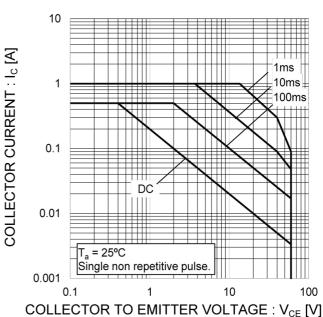
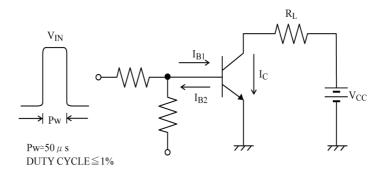
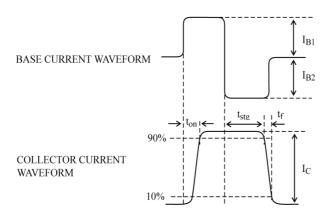


Fig.10 Safe Operating Area



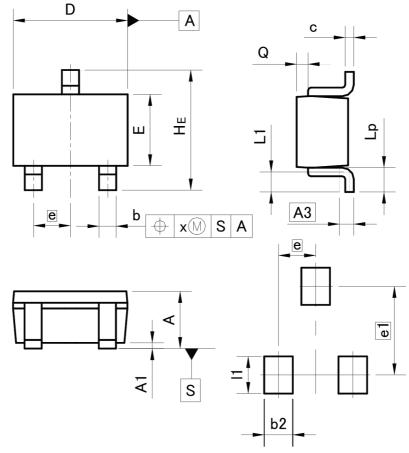
#### SWITCHING TIME TEST CIRCUIT





### Dimensions

UMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
ן ואונט ן	MIN	MAX	MIN	MAX	
Α	0.80	1.00	0.031	0.039	
A1	0.00	0.10	0.000	0.004	
A3	0.5	25	0.0	10	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.65		0.0	26	
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.020	
Lp	0.25	0.55	0.010	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	ı	0.004	

DIM	MILIM	ETERS	INCHES		
MIN		MAX	MIN	MAX	
b2	-	0.50	-	0.020	
e1	1.5	55	0.0	061	
11	-	0.65	ı	0.026	

Dimension in mm/inches



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